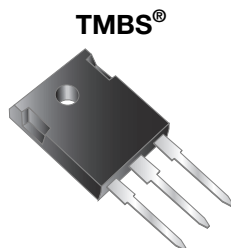




Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.43 \text{ V}$ at $I_F = 10 \text{ A}$



TO-3PW



FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Solder dip 275 °C max. 10 s, per JESD 22-B106
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 40 A
V_{RRM}	100 V
I_{FSM}	450 A
E_{AS} at $L = 180 \text{ mH}$	700 mJ
V_F at $I_F = 40 \text{ A}$	0.64 V
T_J max.	150 °C

MECHANICAL DATA

Case: TO-3PW

Molding compound meets UL 94 V-0 flammability rating
Base P/N-M3 - halogen-free and RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V80100PW	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	100	V
Maximum average forward rectified current (fig. 1)	$I_{F(AV)}$	80	A
		40	
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	450	A
Non-repetitive avalanche energy at $T_J = 25 \text{ °C}$, $L = 180 \text{ mH}$ per diode	E_{AS}	700	mJ
Peak repetitive reverse current at $t_p = 2 \text{ } \mu\text{s}$, 1 kHz, $T_J = 38 \text{ °C} \pm 2 \text{ °C}$ per diode	I_{RRM}	1.0	A
Voltage rate of change (rated V_R)	dV/dt	10 000	V/ μs
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150	°C

V80100PW

Vishay General Semiconductor



ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 1.0 mA	T _A = 25 °C	V _{BR}	100 (minimum)	-	V
Instantaneous forward voltage per diode	I _F = 10 A	T _A = 25 °C	V _F ⁽¹⁾	0.49	-	V
	I _F = 20 A			0.59	-	
	I _F = 40 A			0.76	0.84	
	I _F = 10 A	T _J = 125 °C		0.43	-	
	I _F = 20 A			0.55	-	
	I _F = 40 A			0.64	0.76	
Reverse current per diode	V _R = 80 V	T _A = 25 °C	I _R ⁽²⁾	38	-	μA
		T _A = 125 °C		17	-	mA
	V _R = 100 V	T _A = 25 °C		85	1000	μA
		T _A = 125 °C		33	76	mA

Notes

(1) Pulse test: 300 μs pulse width, 1 % duty cycle(2) Pulse test: Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)				
PARAMETER		SYMBOL	V80100PW	UNIT
Typical thermal resistance	per diode	$R_{\theta JC}$	1.5	$^{\circ}\text{C/W}$
	per device		0.8	

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-3PW	V80100PW-M3/4W	4.5	4W	30/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

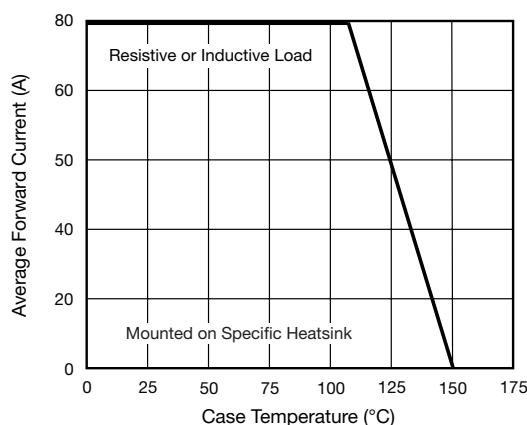
($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Fig. 1 - Forward Current Derating Curve

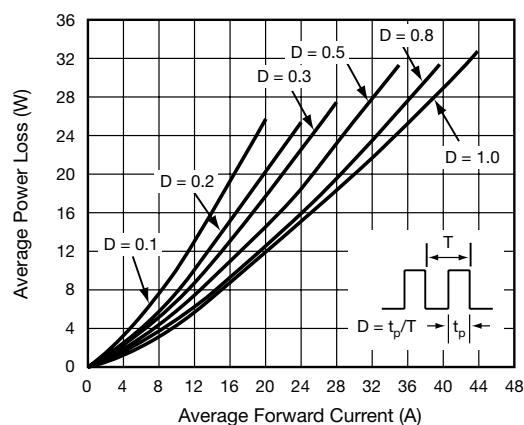


Fig. 2 - Forward Power Loss Characteristics Per Diode

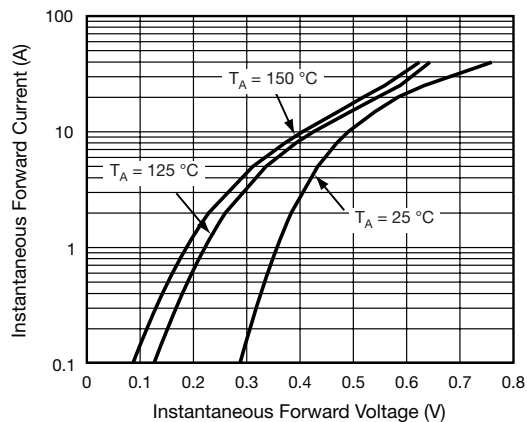


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

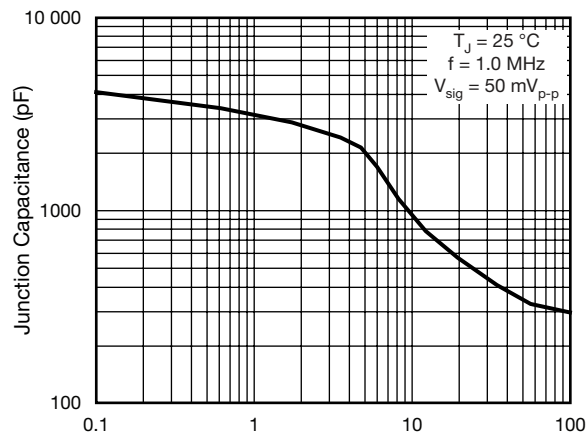


Fig. 5 - Typical Junction Capacitance Per Diode

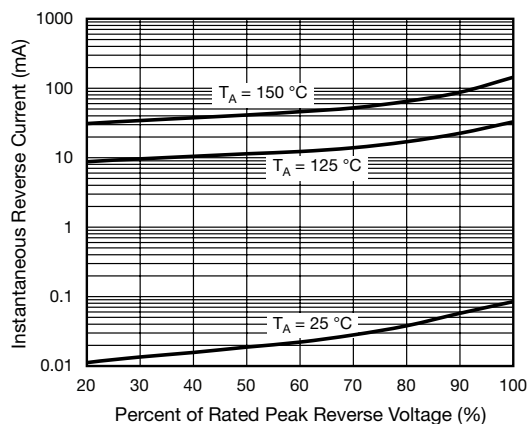


Fig. 4 - Typical Reverse Characteristics Per Diode

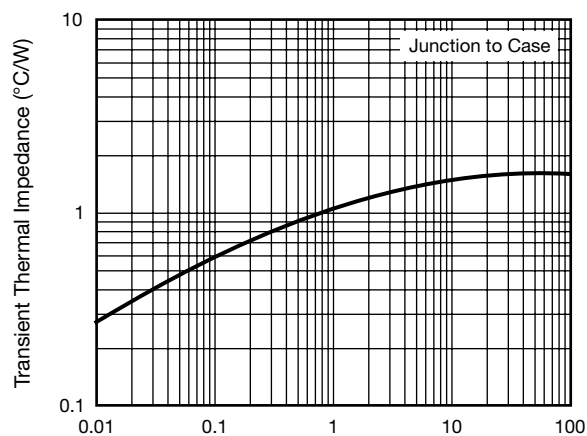
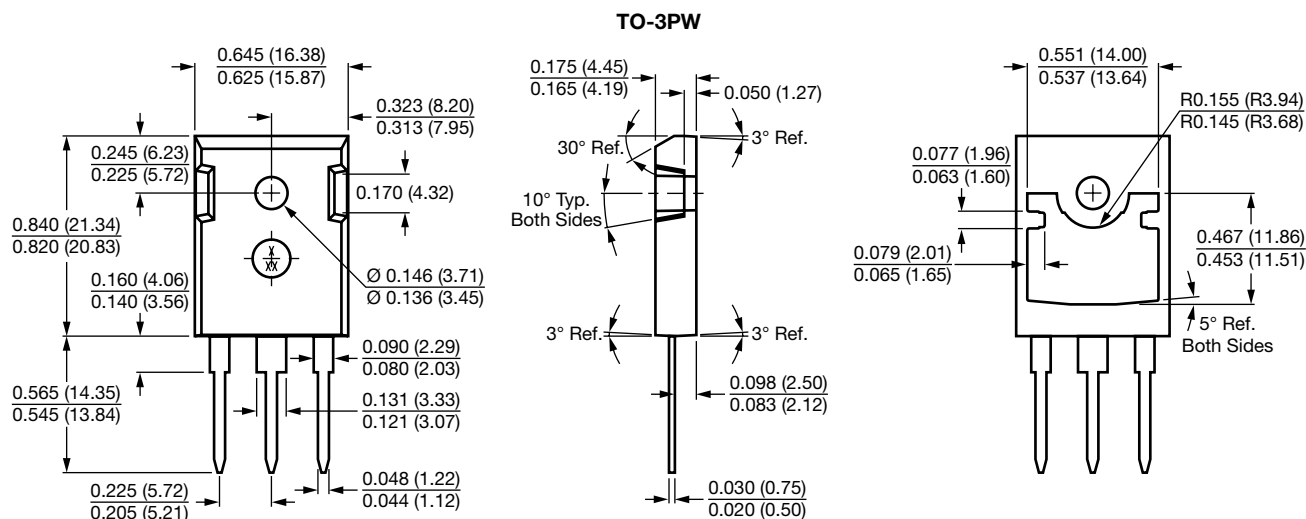


Fig. 6 - Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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